

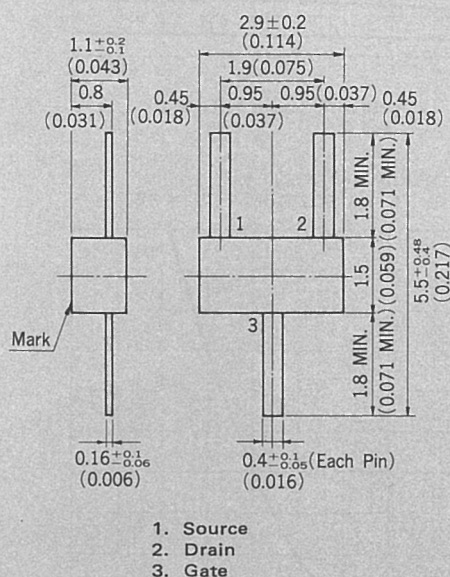
IMPEDANCE CONVERTOR

N-CHANNEL SILICON JUNCTION FIELD EFFECT TRANSISTOR

MINI MOLD

PACKAGE DIMENSIONS

in millimeters (inches)



FEATURES

- Low zero gate voltage drain current: $I_{DSS}=200 \mu A$ TYP.
- High forward transfer admittance:
 $|y_{fs2}| = 1500 \mu S$ TYP. ($V_{DS} = 5.0 V$, $V_{GS}=0$)

ABSOLUTE MAXIMUM RATINGS

Maximum Voltage and Currents ($T_a=25^\circ C$)

Drain to Source Voltage ($V_{GS}=-1.0 V$)	V_{DSX}	20	V
Gate to Drain Voltage	V_{GDO}	-20	V
Gate Current	I_G	10	mA
Drain Current (DC)	I_D	10	mA

Maximum Power Dissipation

Total Power Dissipation at $25^\circ C$ Ambient Temperature	P_T	80	mW
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Maximum Temperatures

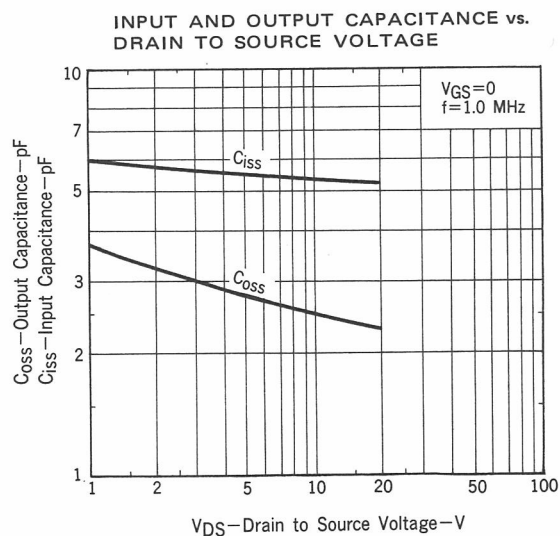
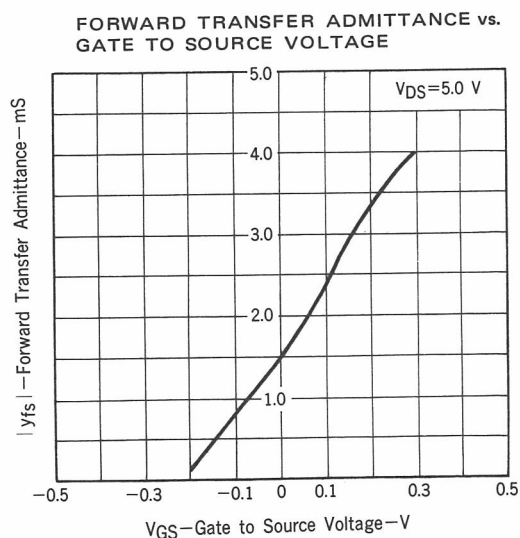
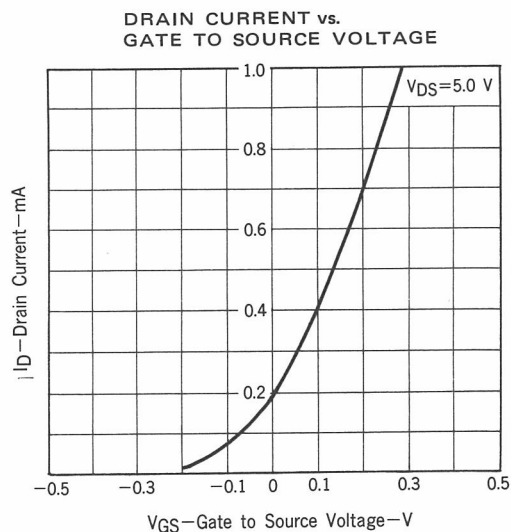
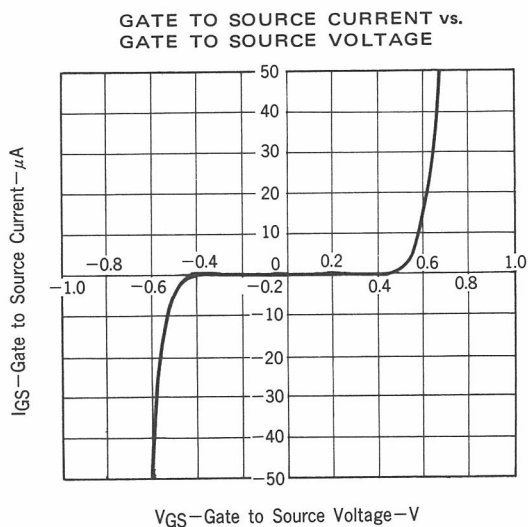
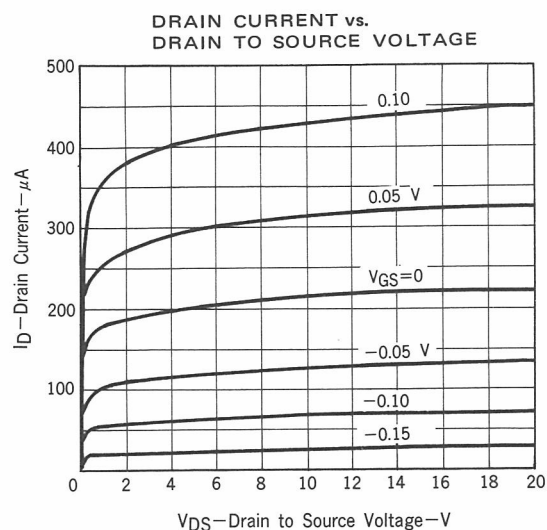
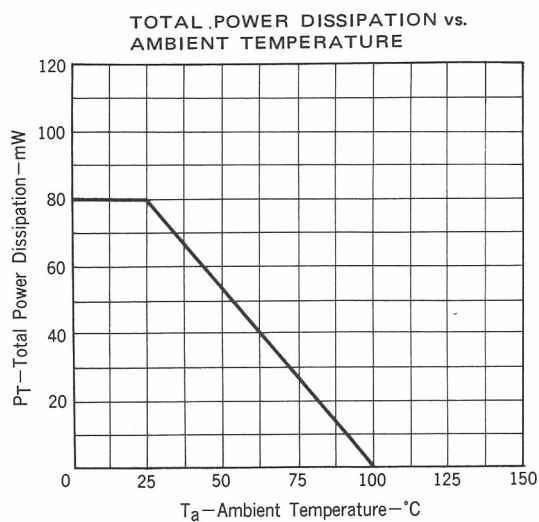
Junction Temperature	T_j	100	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to +100	$^\circ C$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

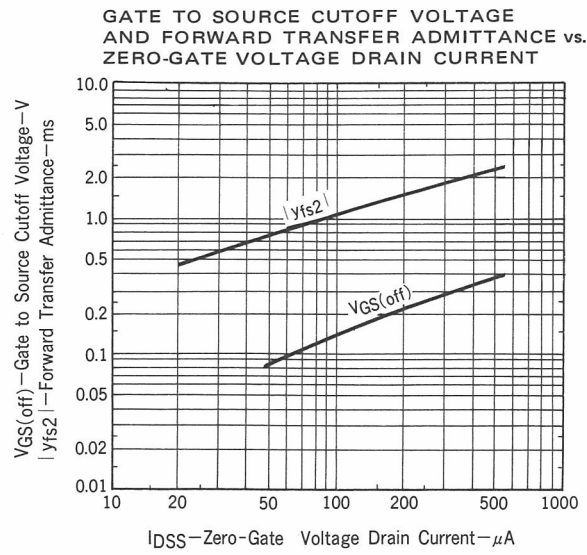
CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Zero-Gate Voltage Drain Current	I_{DSS}	20		540	μA	$V_{DS}=5.0 V$, $V_{GS}=0$
Gate to Source Cutoff Voltage	$V_{GS(off)}$			-0.8	V	$V_{DS}=5.0 V$, $I_D=1.0 \mu A$
Forward Transfer Admittance	$ y_{fs1} $	350			μS	$V_{DS}=5.0 V$, $I_D=30 \mu A$, $f=1.0 kHz$
	$ y_{fs2} $		1500		μS	$V_{DS}=5.0 V$, $V_{GS}=0$, $f=1.0 kHz$
Input Capacitance	C_{iss}		5.5		pF	$V_{DS}=5.0 V$, $V_{GS}=0$, $f=1.0 MHz$
Output Capacitance	C_{oss}		2.7		pF	

I_{DSS} Classification

MARK	J2	J3	J4	J5	J6	J7
$I_{DSS} (\mu A)$	20 - 40	35 - 70	60 - 120	100 - 200	150 - 300	270 - 540

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Phase-out/Discontinued



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